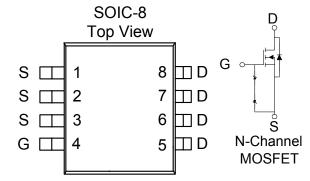
N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
V _{DS} (V)	$r_{\mathrm{DS}(\mathrm{on})} \mathrm{m}(\Omega)$ I_{D} (A)				
30	$22 @ V_{GS} = 10V$	9.4			
	$30 @ V_{GS} = 4.5V$	7.0			

- $\begin{array}{ll} \bullet & \quad \text{Low } r_{DS(on)} \text{ provides higher efficiency and} \\ \text{extends battery life} \end{array}$
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage			30	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current ^a	$T_A=25^{\circ}C$] . т_	9.4			
Continuous Drain Current	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	1D	7.4	A		
Pulsed Drain Current ^b	I_{DM}	±30				
Continuous Source Current (Diode Conduction) ^a	I_S	1.6	A			
D D a	$T_A=25^{\circ}C$	D_	3.1	W		
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	Гр	2			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
N	t <= 10 sec	D	50	°C/W		
Maximum Junction-to-Ambient ^a	Steady State	$R_{ heta JA}$	92	°C/W		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Dayamatay	Symbol	T4 C 14	Limits			T I: 4	
Parameter	Symbol	Test Conditions		Typ	Max	Unit	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \ V, \ V_{GS} = \pm 20 \ V$			±100	nA	
Zero Gate Voltage Drain Current	I	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$		1 25		uA	
-	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$					
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			A	
Drain-Source On-Resistance ^A		$V_{GS} = 10 \text{ V}, I_D = 9.2 \text{ A}$			22	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 7 \text{ A}$			30		
Forward Tranconductance ^A	${f g}_{ m fs}$	$V_{DS} = 15 \text{ V}, I_D = 9.2 \text{ A}$		40		S	
Diode Forward Voltage	V_{SD}	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic ^b							
Total Gate Charge	Q_{g}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$		4.0			
Gate-Source Charge	Q_{gs}	$V_{DS} - 10 V$, $V_{GS} - 4.5 V$, $I_D = 7 A$		1.1		nC	
Gate-Drain Charge	Q_{gd}	$I_{\rm D} - / A$		1.4		1	
Turn-On Delay Time	$t_{d(on)}$			16			
Rise Time	$t_{\rm r}$	$V_{DD} = 10 \text{ V}, R_L = 6 \Omega, ID = 1 \text{ A},$		5		nS	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}$		23		113	
Fall-Time	t_{f}			3			

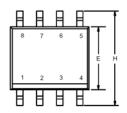
Notes

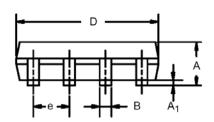
- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Package Information

SO-8: 8LEAD





	MILLIN	IETERS	INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
В	0.35	0.51	0.014	0.020
С	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

